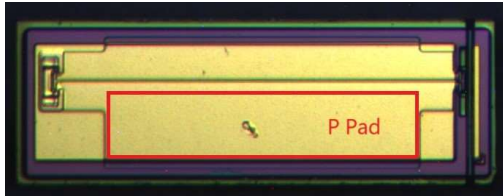


Vertical Emission Laser Chip

VL14000010



Feature

- High power and efficiency
- Cathode bond pad on bottom side.
- Operation temperature -40~85°C

Device Electro-Optical Characteristics

All parameters for T = 25°C unless otherwise noted.

PARAMETER	SYMBOL	UNIT	MIN.	TYP.	MAX.	TEST CONDITIONS
Output power	P	mW	80			I = 100mA
Operating Voltage	V _f	Volt	1.2	1.5	2	I = 100mA
Wavelength	λ	nm	1400		1500	I = 100mA

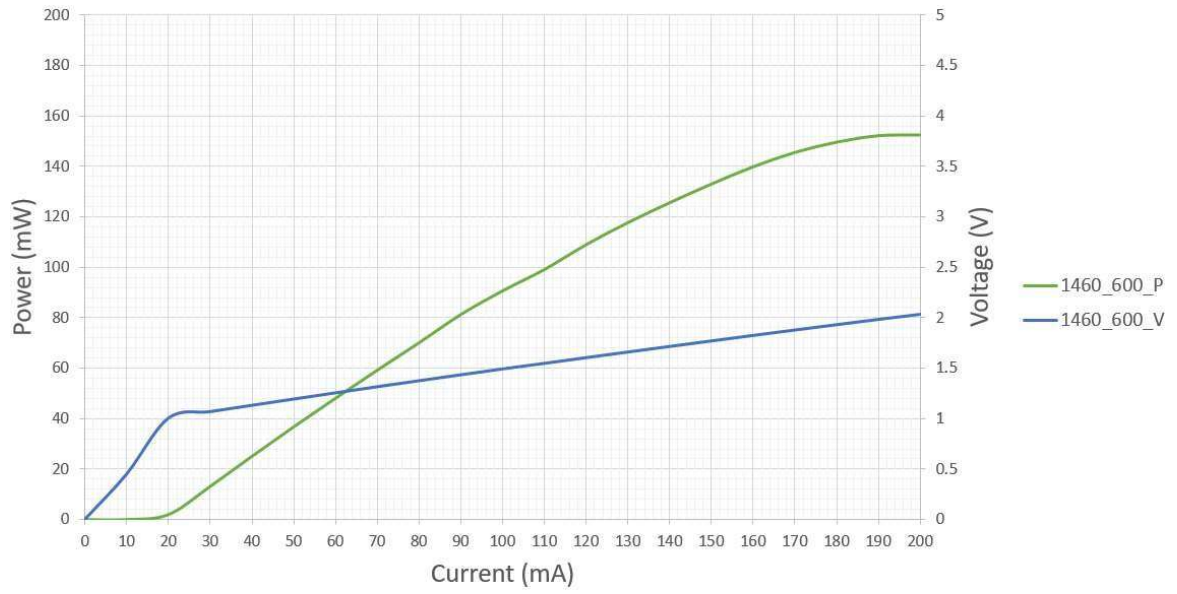
Device Physical Specifications Single Chip

PARAMETER	UNIT	MIN.	TYP.	MAX.
Bond Pad	um	440*80	450*85	460*90
Chip size	um	685X215	700X235	705X240
Chip Hight	um	135	150	165

Absolute Maximum Ratings

PARAMETER	SYMBOL	UNIT	Ratings
Forward Current	I	mA	150
Reverse Voltage	V _r	Volt	1
Operating Temperature	T _o	°C	-40 to +85
Storage Temperature (Chip on Tape)	T _{st}	°C	5 to +35
Soldering Temperature	T _{so}	°C	260 @10sec

Typical LIV Curve



Order Information

VL14000010-A01: Vertical Emission Laser Chip